

S/N 08/903,486

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: W. Mintel

Serial No.: 08/903,486

Group Art Unit: 2811

Filed: July 29, 1997

Docket: 303.326US1

Title: SILICON CARBIDE GATE TRANSISTOR



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AMENDMENT AND RESPONSE

Box RCE
Commissioner for Patents
Washington, D.C. 20231

The applicant has reviewed the Office Action mailed June 6, 2000. Please amend the application as follows:

IN THE CLAIMS

Please cancel claims 6, 7, 23, 30, 36, 49 and 54 and amend the claims as follows:

Sub
D, E, F
1. [Twice Amended] A transistor comprising:
a source region, a drain region, and a channel region between the source and drain regions in a semiconductor surface layer formed on an underlying insulating portion, and an electrically interconnected gate formed of a silicon carbide [material] compound $\text{Si}_{1-x}\text{C}_x$, wherein x is less than 0.5, the gate being connected to receive an input signal.

Sub
E, F
D2
11. [Twice Amended] An integrated circuit device comprising:
a substrate;
a p-channel transistor formed in a first portion of the substrate, the p-channel transistor including a source region, a drain region, a channel region between the source and drain regions, and an electrically interconnected silicon carbide gate over the channel region and separated therefrom by an insulating layer, the gate of the p-channel transistor comprising a silicon carbide compound $\text{Si}_{1-x}\text{C}_x$, wherein x is less than 0.5, and being connected to receive a first input signal;
and
an n-channel transistor formed in a second portion of the substrate, the n-channel transistor including a source region, a drain region, a channel region between the source and drain regions, and an electrically interconnected silicon carbide gate over the channel region and separated therefrom by an insulating layer, the gate of the n-channel transistor comprising a